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MOS INTEGRATED CIRCUIT μ PD720133

USB2.0 to IDE Bridge



The μ PD720133 is designed to function as a bridge between USB 2.0 and ATA/ATAPI. The μ PD720133 complies with the Universal Serial Bus Specification Revision 2.0 full-/high-speed signaling and works up to 480 Mbps. The μ PD720133 consists of a CISC processor, an ATA/ATAPI controller, an endpoint controller (EPC), a serial interface engine (SIE), and an USB2.0 transceiver. The USB2.0 protocol and class specific protocols (bulk only protocol) are handled by the USB2.0 transceiver, the SIE and the EPC. The V30MZ CISC processor in the μ PD720133 takes care of the activities in the transport layer. The firmware controlling the μ PD720133 is located in an embedded ROM.

FEATURES

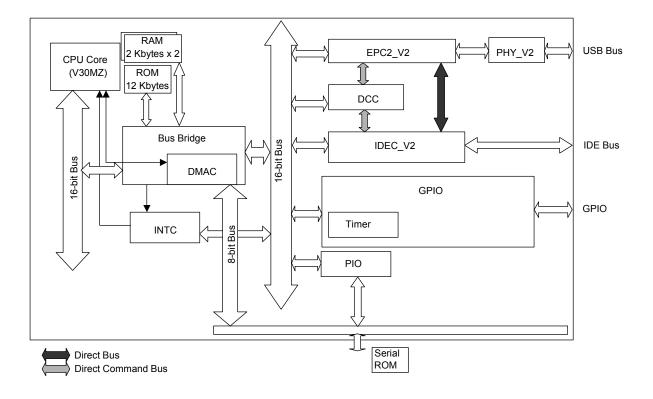
- Compliant with Universal Serial Bus Specification Revision 2.0 (Data Rate 12/480 Mbps)
- Compliant with ATA/ATAPI-6 (LBA48, PIO Mode 0-4, Multi Word DMA Mode 0-2, Ultra DMA Mode 0-4)
- · USB2.0 high-speed bus powered device capability
- Certified by USB implementers forum and granted with USB 2.0 high-speed Logo (TID: 40001985)
- · One USB2.0 high-speed transceiver / receiver with full-speed transceiver / receiver
- USB2.0 High-speed or Full-speed packet protocol sequencer (Serial Interface Engine)
- · Automatic chirp assertion and full-/high-speed mode change
- USB Reset, Suspend and Resume signaling detection
- · Supports power control functionality for IDE device as CD-ROM and HDD
- Supports set feature (TEST_MODE) functionality
- System Clock is generated by 30 MHz X'tal
- 2.5 V and 3.3 V power supply

★ ORDERING INFORMATION

Part Number	Package
μPD720133GB-YEU-A	64-pin plastic TQFP (fine pitch) (10 \times 10) Lead-free product
μPD720133GB-YEU-Y	64-pin plastic TQFP (fine pitch) (10 \times 10) High heat-resistance product

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BLOCK DIAGRAM

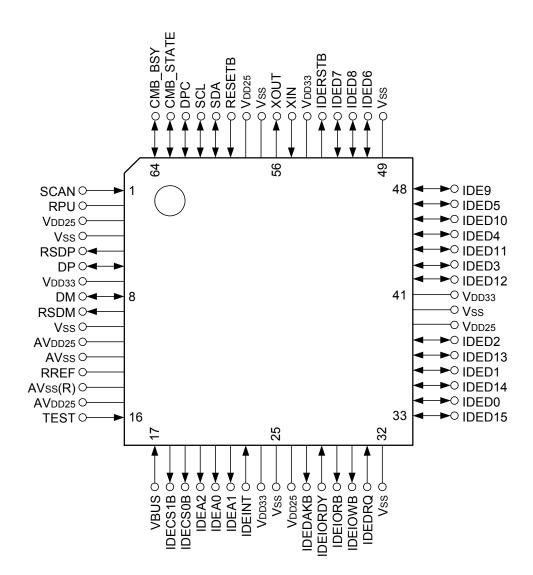


V30MZ	: CISC CPU core
RAM	: 4-Kbyte work RAM for firmware
ROM	: 12-Kbyte ROM for built-in firmware
PHY_V2	: USB2.0 transceiver with serial interface engine
EPC2_V2	: Endpoint controller
IDEC_V2	: IDE controller
DCC	: ATA direct command controller
Bus Bridge	: Internal / external bus controller and DMA controller
INTC	: Interrupt controller (82C59 like)
GPIO	: General purpose 3-bit I/O controller
PIO	: Multipurpose 2-bit I/O controller

PIN CONFIGURATION (TOP VIEW)

- 64-pin plastic TQFP (fine pitch) (10 × 10)
- # μPD720133GB-YEU-A

μPD720133GB-YEU-Y



Pin No	Pin Name						
1	SCAN	17	VBUS	33	IDED15	49	Vss
2	RPU	18	IDECS1B	34	IDED0	50	IDED6
3	VDD25	19	IDECS0B	35	IDED14	51	IDED8
4	Vss	20	IDEA2	36	IDED1	52	IDED7
5	RSDP	21	IDEA0	37	IDED13	53	IDERSTB
6	DP	22	IDEA1	38	IDED2	54	Vdd33
7	Vdd33	23	IDEINT	39	VDD25	55	XIN
8	DM	24	Vdd33	40	Vss	56	XOUT
9	RSDM	25	Vss	41	Vdd33	57	Vss
10	Vss	26	VDD25	42	IDED12	58	Vdd25
11	AVDD25	27	IDEDAKB	43	IDED3	59	RESETB
12	AVss	28	IDEIORDY	44	IDED11	60	SDA (PIO0)
13	RREF	29	IDEIORB	45	IDED4	61	SCL (PIO1)
14	AVss(R)	30	IDEIOWB	46	IDED10	62	DPC(GPIO5)
15	AVDD25	31	IDEDRQ	47	IDED5	63	CMB_STATE(GPIO6)
16	TEST	32	Vss	48	IDED9	64	CMB_BSY(GPIO7)

Remark AVss(R) should be used to connect RREF through 1 % precision reference resistor of 2.43 k Ω .

1. PIN INFORMATION

Pin Name	I/O	Buffer Type	Active Level	Function
XIN	Ι	2.5 V Input		System clock input or oscillator In
XOUT	0	2.5 V Output		Oscillator out
RESETB	I	3.3 V Schmitt Input	Low	Asynchronous reset signaling
IDECS(1:0)B	0 (I/O)	5 V tolerant Output	Low	IDE host chip select
IDEA(2:0)	O (I/O)	5 V tolerant Output		IDE address bus
IDEINT	Ι	5 V tolerant Input	High	IDE interrupt request from device to host
IDEDAKB	O (I/O)	5 V tolerant Output	Low	IDE DMA acknowledge
IDEIORDY	I	5 V tolerant Input	High	IDE IO channel ready
IDEIORB	O (I/O)	5 V tolerant Output	Low	IDE IO read strobe
IDEIOWB	O (I/O)	5 V tolerant Output	Low	IDE IO write strobe
IDEDRQ	Ι	5 V tolerant Input	High	IDE DMA request from device to host
IDED(15:0)	I/O	5 V tolerant I/O		IDE data bus
IDERSTB	O (I/O)	5 V tolerant Output	Low	IDE reset from host to device
CMB_BSY (GPIO7)	I/O	3.3 V I/O		Combo IDE bus busy
CMB_STATE (GPIO6)	I/O	3.3 V I/O		Combo IDE bus state
DPC (GPIO5)	I/O	3.3 V I/O		Power control signaling for IDE device
SDA (PIO0)	I/O	3.3 V I/O		Serial ROM data signaling
SCL (PIO1)	I/O	3.3 V I/O		Serial ROM clock signaling
VBUS	I	5 V Schmitt Input Note		VBUS monitoring
DP	I/O	USB high speed D+ I/O		USB's high speed D+ signal
DM	I/O	USB high speed D– I/O		USB's high speed D– signal
RSDP	0	USB full speed D+ Output		USB's full speed D+ signal
RSDM	0	USB full speed D- Output		USB's full speed D– signal
RPU	А	USB Pull-up control		USB's 1.5 k Ω pull-up resistor control
RREF	А	Analog		Reference resistor
SCAN	I	3.3 V Input		Scan mode control
TEST	I	3.3 V Input		Test mode setting
AV _{DD25}				2.5 V VDD for Analog circuit
VDD25				2.5 V VDD
VDD33				3.3 V VDD
AVss				Vss for Analog circuit
Vss				Vss

Note VBUS pin may be used to monitor for VBUS line even if V_{DD33}, V_{DD25}, and AV_{DD25} are shut off. The System Designer must ensure that the input voltage level for VBUS pin is less than 3.0 V. [that is the absolute maximum rating].

- Remarks 1. "5 V tolerant" means that the buffer is a 3.3 V buffer with 5 V tolerant circuit.
 - 2. The signal marked as "(I/O)" in the above table operates as I/O signals during testing. They should be ignored under normal operation.

2. FUNCTION INFORMATION

The USB to IDE system can be realized by μ PD720133. If the customizations of data such as USB vendor ID and USB product ID are required, an external serial ROM can be used. The μ PD720133 also has power circuit to turn on and off the system power supply. The μ PD720133 can operate in either bus-powered mode or self-powered mode. If the total power consumption of the USB to IDE system within the USB 2.0 specification of a bus powered device, it will be possible to realize a high-speed capable bus powered system. In addition, μ PD720133 has a feature of IDE bus arbitration. This enables system, which has two IDE controllers to control a single IDE device. In this case, another IDE controller also must have a feature of IDE bus arbitration.

The setting of IDE controller in the μ PD720133 is controlled by data in serial ROM.

2.1 Data in Serial ROM

The μ PD720133 loads some data such as Vendor ID, Product ID and some additional USB related information, etc from serial ROM during μ PD720133 initialization.

Offset (H)	Data Size	Symbol	Description
+00	1 Word	idMark	Validation Mark of 55AAH
+02	1 Word	CheckSum	Check sum of serial ROM
+04	1 Word	Flags	Control for descriptor overwrite
+06	1 Byte	ModeReset	PWR, CLC, DCC, DV[1:0], DPC Reset bit map field
+07	1 Byte	ModeSet	PWR, CLC, DCC, DV[1:0], DPC Set bit map field
+08	1 Word	idVendor	idVendor field in Device descriptor
+0A	1 Word	idProduct	idProduct field in Device descriptor
+0C	1 Word	bcdDevice	bcdDevice field in Device descriptor
+0E	1 Word	Reserved	Reserved for future use.
+10	1 Byte	MaxPower Bus	bMaxPower field in Configuration descriptor for Bus powered mode
+11	1 Byte	MaxPower Self	bMaxPower field in Configuration descriptor for Self powered mode
+12	1 Byte	bInterfaceClass	bInterfaceClass field in Interface descriptor
+13	1 Byte	bInterfaceSubClass	bInterfaceSubClass field in Interface descriptor
+14	1 Byte	bInterfaceProtocol	bInterfaceProtocol field in Interface descriptor
+15	1 Byte	Reserved	Reserved for future use.
+16	1Word	TxModeReset	IDE transmission type such as Ultra DMA 66 Reset bit map field
+18	1Word	TxModeSet	IDE transmission type such as Ultra DMA 66 Set bit map field
+1A	1Word	RompatchSW	ROM Patch information (Patch On or Off) of External Function
+1C	4 Bytes	Reserved	Reserved for future use.
+20	32 Bytes	ManufactureString	String descriptor for Manufacturer
+40	32 Bytes	ProductString	String descriptor for Product
+60	32 Bytes	SerialString	String descriptor for Device serial number
+80	$128 \times n$ Bytes	FW Patch	Firmware patch module for self-powered/bus-powered mode

Table 2-1. Data in Serial ROM

2.2 Pin Setting

Settings of the SCL, SDA and unused pins (TEST and SCAN) are recommended as follows. Please note that the setting of the SCL depends on size of Serial ROM.

Pin Name	Setting
SCL	Pull Up ^{Note}
SDA	Pull Up
TEST	Low Clamp
SCAN	Low Clamp

Table	2-2.	Pin	Settings
			ooungo

Note If serial ROM size is more than 2 Kbytes, SCL should be pull down.

The settings for any other pins such as the CMB_BSY and the CMB_STATE depend on USB2.0 to IDE Bridge system. For example, if two IDE controllers are implemented in the system to control one target IDE device and one of the two IDE controllers is the μ PD720133, then both the CMB_BSY and the CMB_STATE are used to handshake between the two IDE controller chips. On the other hand, when the system uses the μ PD720133 as the only IDE controller to control a target IDE device, then both the CMB_BSY and the CMB_STATE should be connected to ground.

2.3 Control Bit in Serial ROM

The following tables show IDE status and control bit in serial ROM.

No.	Device Power	Internal Clock	ΑΤΑ/ΑΤΑΡΙ	PWR	CLC	DV1	DV0
0	Bus Powered	7.5 MHz	No device connected	1	1	1	1
1			ATA	1	1	1	0
2			ATAPI	1	1	0	1
3			Reserved	1	1	0	0
4		60 MHz	No device connected	1	0	1	1
5			ATA	1	0	1	0
6			ATAPI	1	0	0	1
7			Reserved	1	0	0	0
8	Self Powered	60 MHz	No device connected	0	1	1	1
9			Combo (ATA)	0	1	1	0
10			Combo (ATAPI)	0	1	0	1
11			Combo auto device detect	0	1	0	0
12			No device connected	0	0	1	1
13			ATA	0	0	1	0
14			ATAPI	0	0	0	1
15			Auto device detect	0	0	0	0

Table 2-3. DV1/DV0, CLC, PWR Setting

Remarks 1. Setting of no. 0, 3, 4, 7, 8, and 12 are not allowed.

- **2.** For bus powered setting, some critical considerations such as power consumption for the total system should be observed.
- 3. The slave device function cannot use Auto device detect.

	Condition			DCC	Description
DV1	DV0	Mode	Target Device	setting in Serial ROM	
1	0	ΑΤΑ	ΑΤΑ	Reset Set	Ultra, Multi Word DMA are disabled. Ultra, Multi Word DMA are enabled.
0	1	ATAPI	ATAPI	Reset Set	Ultra DMA are disabled. Ultra, Multi Word DMA are enabled.
0	0	Auto device	ΑΤΑ	Reset Set	Ultra, Multi Word DMA are disabled. Ultra, Multi Word DMA are enabled.
		detect	ATAPI	Reset Set	Ultra DMA are disabled. Ultra, Multi Word DMA are enabled.

Table 2-4. DV1/DV0, DCC Setting

Remark PIO mode 0-4 are always enabled.

2.4 Combo Mode Function

The μ PD720133 can be used to realize that two IDE controller chips control one target IDE device in one system. In order to realize IDE bus arbitration between two IDE controller chips, the μ PD720133 has the CMB_BSY and the CMB_STATE. Combo mode is enabled when PWR = 0 and CLC = 1.

CMB_BSY and CMB_STATE are connected to another IDE controller chip as shown below.



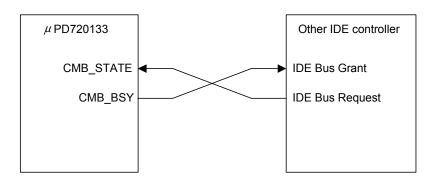
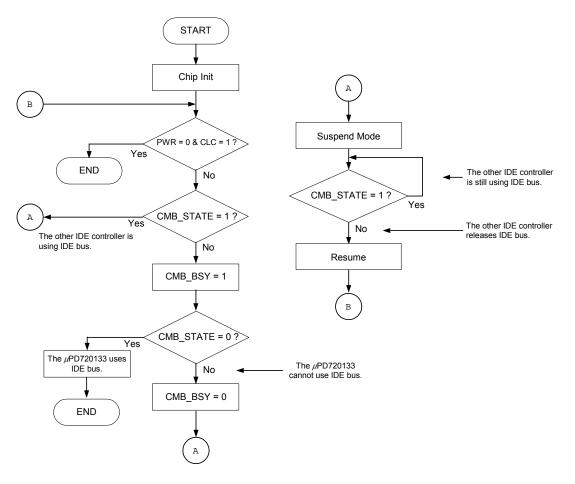


Table 2-5. Description of CMB_BSY and CMB_STATE

Pin Name	Direction	Value	Description
CMB_STATE	IN	0 Other IDE controller does not require or does not use IDE b	
		1	Other IDE controller requires or is using IDE bus.
CMB_BSY	OUT	0 The µPD720133 does not require or does not use IDE b	
		1	The μ PD720133 requires or is using IDE bus.

The IDE bus arbitration will be performed in the following sequence. The μ PD720133 will check if the other IDE controller is using the IDE bus. If the other IDE controller is not using the IDE bus, the μ PD720133 will be able to use the IDE bus. On the other hand, if the other IDE controller is using the IDE bus, the μ PD720133 transmits to the suspend mode. And the μ PD720133 resumes on condition that the CMB_STATE becomes low level. After that, the arbitration will restart from the beginning of the sequence.

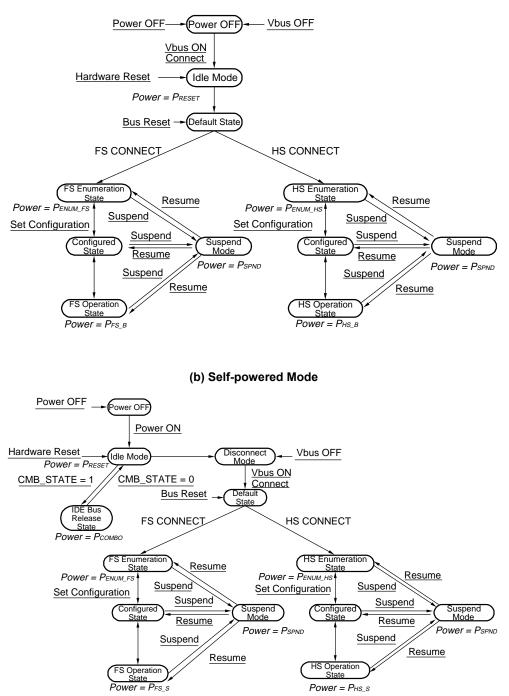




2.5 Power Control

To realize bus-powered or high performance self-powered USB2.0 to IDE Bridge system, the μ PD720133 has two internal system clock mode. One is 7.5 MHz for bus-powered mode and another is 60 MHz for self-powered mode. The μ PD720133 controls the power state by events as follows. The word with under line indicates event. The Italic word indicates the power state.

Figure 2-3. Power State Control



(a) Bus-powered Mode

High impedance state

To realize bus-powered USB2.0 to IDE Bridge system, μ PD720133 has a DPC pin to control the on and off of the IDE device's power supply according to the USB device states. DPC should be pull-up to 3.3 V because DPC output becomes high impedance state until the μ PD720133 is initialized.

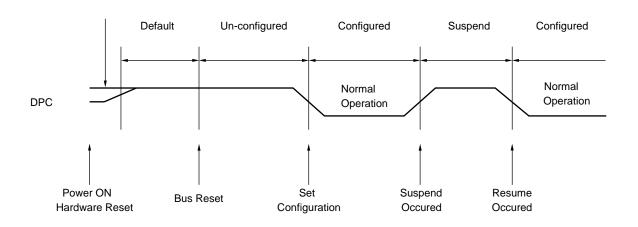
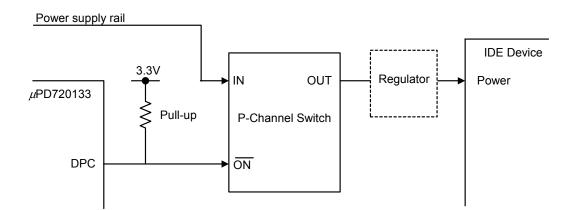


Figure 2-4. DPC Pin to Control IDE Device's Power Circuit

The following example is a circuit for controlling the power supplies to IDE device while the μ PD720133 is under default and un-configured state. Also, the power supply to IDE device is disabled during suspend state.

Power consumption of total system under default, un-configured, and suspend state can be reduced by DPC pin.





3. ELECTRICAL SPECIFICATIONS

- 3.1 Buffer List
 - 2.5 V oscillator interface

XIN, XOUT

• 3.3 V input buffer

TEST, SCAN

• 3.3 V schmitt input buffer

RESETB

• 3.3 V IoL = 3 mA bi-directional buffer with input enable (OR-type)

SDA, SCL, DPC (GPIO5), CMB_STATE (GPIO6), CMB_BSY (GPIO7)

• 5 V schmitt input buffer

VBUS

5 V IoL = 6 mA bi-directional buffer with input enable (OR-type)
IDED(15:0), IDEINT, IDEIORDY, IDEDRQ, IDECS(1:0)B, IDEA(2:0), IDEDAKB, IDEIORB, IDEIOWB,

IDERSTB

USB interface

DP, DM, RSDP, RSDM, RREF, RPU

Remark "5 V" refers to a 3.3 V buffer with 5-V tolerant circuit. Therefore, it is possible to have a 5-V connection for an external bus, but the output level will be only up to 3.3 V, which is the VDD33 voltage.

3.2 Terminology

Terms Used in Absolute Maximum Ratings

Parameter	Symbol	Meaning
Power supply voltage	Vdd33, Vdd25	Indicates voltage range within which damage or reduced reliability will not result when power is applied to a V_{DD} pin.
Input voltage	Vı	Indicates voltage range within which damage or reduced reliability will not result when power is applied to an input pin.
Output voltage	Vo	Indicates voltage range within which damage or reduced reliability will not result when power is applied to an output pin.
Output current	lo	Indicates absolute tolerance value for DC current to prevent damage or reduced reliability when a current flows out of or into an output pin.
Operating temperature	Та	Indicates the ambient temperature range for normal logic operations.
Storage temperature	Tstg	Indicates the element temperature range within which damage or reduced reliability will not result while no voltage or current are applied to the device.

Terms Used in Recommended Operating Range

Parameter	Symbol	Meaning
Power supply voltage	Vdd33, Vdd25	Indicates the voltage range for normal logic operations occur when $V_{SS} = 0 V$.
High-level input voltage	Vін	Indicates the voltage, which is applied to the input pins of the device, is the voltage indicates that the high level states for normal operation of the input buffer.
		* If a voltage that is equal to or greater than the "Min." value is applied, the input voltage is guaranteed as high level voltage.
Low-level input voltage	VIL	Indicates the voltage, which is applied to the input pins of the device, is the voltage indicates that the low level states for normal operation of the input buffer.
		* If a voltage that is equal to or lesser than the "Max." value is applied, the input voltage is guaranteed as low level voltage.
Hysteresys voltage	Vн	Indicates the differential between the positive trigger voltage and the negative trigger voltage.
Input rise time	tri	Indicates allowable input rise time to input pins. Input rise time is transition time from $0.1 \times V_{DD}$ to $0.9 \times V_{DD}$.
Input fall time	tfi	Indicates allowable input fall time to input pins. Input fall time is transition time from 0.9 \times V_{DD} to 0.1 \times V_{DD}.

Terms Used in DC Characteristics

Parameter	Symbol	Meaning
Off-state output leakage current	loz	Indicates the current that flows from the power supply pins when the rated power supply voltage is applied when a 3-state output has high impedance.
Output short circuit current	los	Indicates the current that flows when the output pin is shorted (to GND pins) when output is at high-level.
Input leakage current	h	Indicates the current that flows when the input voltage is supplied to the input pin.
Low-level output current	lol	Indicates the current that flows to the output pins when the rated low-level output voltage is being applied.
High-level output current	Іон	Indicates the current that flows from the output pins when the rated high-level output voltage is being applied.

3.3 Electrical Specifications

Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating	Unit
Power supply voltage	VDD33	3.3 V power supply rail	-0.5 to +4.6	V
	VDD25	2.5 V power supply rail	-0.5 to +3.6	V
Input voltage, 5 V buffer	Vı	$\begin{array}{l} 3.0 \; V \leq V_{\text{DD33}} \leq 3.6 \; V \\ V_{\text{I}} < V_{\text{DD33}} + 3.0 \; V \end{array}$	-0.5 to +6.6	V
Input voltage, 3.3 V buffer	Vı	$\begin{array}{l} 3.0 \; V \leq V_{DD33} \leq 3.6 \; V \\ V_{I} < V_{DD33} + 1.0 \; V \end{array}$	-0.5 to +4.6	V
Input voltage, 2.5 V buffer	Vı	$\begin{array}{l} 2.3 \ V \leq V_{DD25} \leq 2.7 \ V \\ V_1 < V_{DD25} + 0.9 \ V \end{array}$	-0.5 to +3.6	V
Output voltage, 5 V buffer	Vo	$\begin{array}{l} 3.0 \; V \leq V_{\text{DD33}} \leq 3.6 \; V \\ V_0 < V_{\text{DD33}} + 3.0 \; V \end{array}$	-0.5 to +6.6	V
Output voltage, 3.3 V buffer	Vo	$\begin{array}{l} 3.0 \; V \leq V_{\text{DD33}} \leq 3.6 \; V \\ V_0 < V_{\text{DD33}} + 1.0 \; V \end{array}$	-0.5 to +4.6	V
Output voltage, 2.5 V buffer	Vo	$\begin{array}{l} 2.3 \ V \leq V_{DD25} \leq 2.7 \ V \\ V_0 < V_{DD25} + 0.9 \ V \end{array}$	-0.5 to +3.6	V
Output current, 5 V buffer	lo	IoL = 6 mA	20	mA
Output current, 3.3 V buffer	lo	IoL = 6 mA	20	mA
		lo∟ = 3 mA	10	mA
Operating ambient temperature	TA		0 to +70	°C
Storage temperature	Tstg		-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameters. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

The ratings and conditions indicated for DC characteristics and AC characteristics represent the quality assurance range during normal operation.

Two Power Supply Rails Limitation

The μ PD720133 has two power supply rails (2.5 V, 3.3 V). The system will require the power supply rail to be stable at V_{DD} level by a specified time. However, there are difference between the time of V_{DD25} and V_{DD33} becoming stable. The μ PD720133 requires that V_{DD25} becomes stable before V_{DD33}. Also, it is necessary that V_{DD33} be powered within 100 ms after V_{DD25} became stable. In any case, the system must ensure that the absolute maximum ratings for V₁ / V₀ are not exceeded. System reset signaling must be asserted after the specified time of which both V_{DD25} and V_{DD33} become stable.

Recommended Operating Ranges

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Operating voltage	VDD33	3.3 V for VDD33 pins	3.0	3.3	3.6	V
	VDD25	2.5 V for VDD25 pins	2.3	2.5	2.7	V
	VDD25	2.5 V for AVDD25 pins	2.3	2.5	2.7	V
High-level input voltage	VIH					
5.0 V high-level input voltage			2.0		5.5	V
3.3 V high-level input voltage			2.0		V _{DD33}	V
2.5 V high-level input voltage			1.7		V _{DD25}	V
Low-level input voltage	VIL					
5.0 V low-level input voltage			0		0.8	V
3.3 V low-level input voltage			0		0.8	V
2.5 V low-level input voltage			0		0.7	V
Hysteresis voltage	Vн					
5 V hysteresis voltage			0.3		1.5	V
3.3 V hysteresis voltage			0.2		1.0	V
Input rise time	tri					
Normal buffer			0		200	ns
Schmitt buffer			0		10	ms
Input fall time	tri					
Normal buffer			0		200	ns
Schmitt buffer			0		10	ms

DC Characteristics (VDD33 = 3.0 to 3.6 V, VDD25 = 2.3 to 2.7 V, TA = 0 to +70°C)

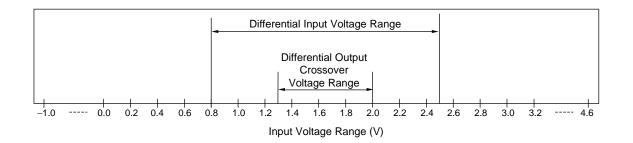
Control Pin Block

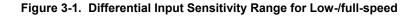
Parameter	Symbol	Condition	Min.	Max.	Unit
Off-state output current	loz	Vo = Vdd33, Vdd25 or Vss		±10	μA
Output short circuit current	los ^{Note}			-250	mA
Low-level output current	lol				
5.0 V low-level output current		Vol = 0.4 V	6.0		mA
3.3 V low-level output current		Vol = 0.4 V	6.0		mA
3.3 V low-level output current		Vol = 0.4 V	3.0		mA
High-level output current	Іон				
5.0 V high-level output current		Vон = 2.4 V	-2.0		mA
3.3 V high-level output current		Vон = 2.4 V	-6.0		mA
3.3 V high-level output current		Vон = 2.4 V	-3.0		mA
Input leakage current	h				
3.3 V buffer		VI = VDD or VSS		±10	μA
5.0 V buffer		VI = VDD or VSS		±10	μA

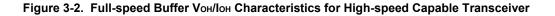
Note It is specified under the assumption that only one pin on the LSI is short-circuited for not more than one second.

USB Interface Block

Parameter	Symbol	Conditions	Min.	Max.	Unit
Serial Resistor between DP (DM) and RSDP (RSDM)	Rs		38.61	39.39	Ω
Output pin impedance	ZHSDRV	Includes Rs resistor	40.5	49.5	Ω
Bus pull-up resistor on upstream facing port	Rpu	$1.5 \text{ k}\Omega \pm 5\%$ consists of resistance of transistor and pull-up resistor	1.485	1.515	Ω
Termination voltage for upstream facing port pull-up	Vterm		3.0	3.6	V
Input Levels for Full-speed:					
High-level input voltage (drive)	VIH		2.0		V
High-level input voltage (floating)	VIHZ		2.7	3.6	
Low-level input voltage	VIL			0.8	V
Differential input sensitivity	VDI	(D+) – (D–)	0.2		V
Differential common mode range	Vсм	Includes VDI range	0.8	2.5	V
Output Levels for Full-speed:					
High-level output voltage	Vон	R∟ of 14.25 kΩ to Vss	2.8	3.6	V
Low-level output voltage	Vol	R∟ of 1.425 kΩ to 3.6 V	0.0	0.3	V
SE1	Vose1		0.8		V
Output signal crossover point voltage	VCRS		1.3	2.0	V
Input Levels for High-speed:					
High-speed squelch detection threshold (differential signal)	VHSSQ		100	150	mV
High-speed disconnect detection threshold (differential signal)	VHSDSC		525	625	mV
High-speed data signaling common mode voltage range	Vнscм		-50	+500	mV
High-speed differential input signaling level	See Figure	3-4 .			
Output Levels for High-speed:					
High-speed idle state	VHSOI		-10.0	+10.0	mV
High-speed data signaling high	Vнsoн		360	440	mV
High-speed data signaling low	VHSOL		-10.0	+10.0	mV
Chirp J level (differential signal)	VCHIRPJ		700	1100	mV
Chirp K level (differential signal)	VCHIRPK		-900	-500	mV







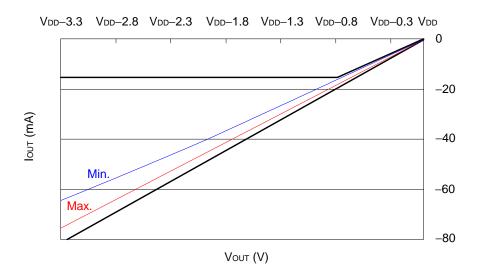
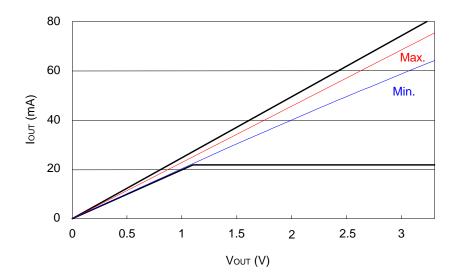


Figure 3-3. Full-speed Buffer VoL/IoL Characteristics for High-speed Capable Transceiver



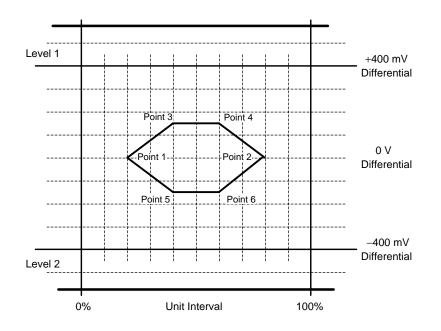
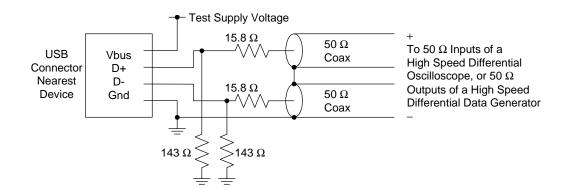


Figure 3-4. Receiver Sensitivity for Transceiver at DP/DM





Pin Capacitance

Parameter	Symbol	Condition	Min.	Max.	Unit
Input capacitance	Cin	V _{DD} = 0 V, T _A = 25°C	4	6	pF
Output capacitance	Соит	fc = 1 MHz	4	6	pF
I/O capacitance	Сю	Unmeasured pins returned to 0 V	4	6	pF

★ Power Consumption

(1) The power consumption when device works as bus-powered mode

Symbol	Condition		Max.		Unit
		Vdd25	Vdd33	AV _{DD25}	
Penum-bus	The power consumption during device unconfigured stage				
	High-speed operating	55	3	10	mA
	Full-speed operating	25	4	10	mA
Pw-bus	The power consumption during device configured stage				
	High-speed operating	100	22	10	mA
	Full-speed operating	75	13	10	mA
Pw_spd-bus	The power consumption under suspend state	15	235	5	μA

(2) The power consumption when device works as self-powered mode

Symbol	Condition		Max.		Unit
		Vdd25	Vdd33	AV _{DD25}	
Penum-self	The power consumption during device unconfigured stage				
	High-speed operating	90	5	10	mA
	Full-speed operating	60	5	10	mA
Pw-self	The power consumption during device configured stage				
	High-speed operating	100	25	10	mA
	Full-speed operating	75	13	10	mA
Pw_spd-self	The power consumption under suspend state	50	500	15	μA
Pw_unp	The power consumption under unplug state	50	500	15	μA
Рw_сом	The power consumption under combo mode	50	500	15	μA
	The device is releasing the IDE bus.				

AC Characteristics (VDD33 = 3.0 to 3.6 V, VDD25 = 2.3 to 2.7 V, TA = 0 to +70°C)

System Clock Ratings

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Clock frequency	fськ	X'tal	–500 ppm	30	+500 ppm	MHz
		Oscillator block	–500 ppm	30	+500 ppm	MHz
Clock duty cycle	t duty		45	50	55	%

Remarks 1. Recommended accuracy of clock frequency is \pm 100 ppm.

2. Required accuracy of X'tal or Oscillator block is including initial frequency accuracy, the spread of X'tal capacitor loading, supply voltage, temperature, and aging, etc.

System Reset signaling

Parameter	Symbol	Conditions	Min.	Max.	Unit
Reset active time	t rst		2		μs

USB Interface Block

					(1/2)
Parameter	Symbol	Conditions	Min.	Max.	Unit
Full-speed Source Electrical Characteristic	cs				
Rise time (10% - 90%)	tfr	CL = 50 pF, Rs = 36 Ω	4	20	ns
Fall time (90% - 10%)	t⊧⊧	CL = 50 pF, Rs = 36 Ω	4	20	ns
Differential rise and fall time matching	t FRFM	(tfr/tff)	90	111.11	%
Full-speed data rate for device which are high-speed capable	t fdraths	Average bit rate	11.9940	12.0060	Mbps
Frame interval	t FRAME		0.9995	1.0005	ms
Consecutive frame interval jitter	t RFI	No clock adjustment		42	ns
Source jitter total (including frequency tolerance):					
To next transition For paired transitions	t _{DJ1} t _{DJ2}		-3.5 -4.0	+3.5 +4.0	ns ns
Source jitter for differential transition to SE0 transition	t fdeop		-2	+5	ns
Receiver jitter: To next transition For paired transitions	tjr1 tjr2		-18.5 -9	+18.5 +9	ns ns
Source SE0 interval of EOP	t feopt		160	175	ns
Receiver SE0 interval of EOP	t feopr		82		ns
Width of SE0 interval during differential transition	tfst			14	ns

					(2/2
Parameter	Symbol	Conditions	Min.	Max.	Unit
High-speed Source Electrical Characterist	ics				
Rise time (10% - 90%)	thsr		500		ps
Fall time (90% - 10%)	thsp		500		ps
Driver waveform	See Figure	3-6.			
High-speed data rate	t HSDRAT		479.760	480.240	Mbps
Microframe interval	t HSFRAM		124.9375	125.0625	μs
Consecutive microframe interval difference	thsrfi			4 high-speed	Bit times
Data source jitter	See Figure	3-6 .			
Receiver jitter tolerance	See Figure	3-4 .			
Device Event Timings					
Time from internal power good to device pulling D+ beyond V _{IHZ} (min.) (signaling attached)	t sigatt			100	ms
Debounce interval provided by USB system software after attach	t attdb			100	ms
Inter-packet delay for full-speed	tipd		2		Bit times
Inter-packet delay for device response w/detachable cable for full-speed	trspipd1			6.5	Bit times
High-speed detection start time from suspend	t sca		2.5		μs
Sample time for suspend vs reset	tcsr		100	875	μs
Time to detect bus suspend state	t spd		3.000	3.125	ms
Power down under suspend	tsus			10	ms
Reversion time from suspend to high-speed	tкнs			1.333	μs
Drive Chirp K width	tско		1		ms
Finish Chirp K assertion	t FCA			7	ms
Start sequencing Chirp K-J-K-J-K-J	tssc			100	μs
Finish sequencing Chirp K-J	t FSC		-500	-100	μs
Detect sequencing Chirp K-J width	tcsi		2.5		μs
Sample time for sequencing Chirp	tscs		1	2.5	ms
Reversion time to high-speed	t RHA			500	μs
High-speed detection start time	tHDS		2.5	3000	μs
Reset completed time	t DRS		10		ms

IDE Interface Block

PIO mode

Parameter	Symbol	Mode 0	Mode 1	Mode 2	Mode 3	Mode 4	Unit
Cycle time (min.)	to	600	383	240	180	120	ns
Address setup time (min.)	t1	70	50	30	30	25	ns
16 bits DIOR/DIOW pulse width (min.)	t2	165	125	100	80	70	ns
8 bits DIOR/DIOW pulse width (min.)		290	290	290	80	70	ns
DIOR/DIOW recovery time (min.)	t2i	_	-		70	25	ns
DIOW data setup time (min.)	tз	60	45	30	30	20	ns
DIOW data hold time (min.)	t4	30	20	15	10	10	ns
DIOR data setup time (min.)	t5	50	35	20	20	20	ns
DIOR data hold time (min.)	t6	5	5	5	5	5	ns
DIOR 3-state delay time (max.)	t _{6Z}	30	30	30	30	30	ns
Address hold time (min.)	to	20	15	10	10	10	ns
IORDY read data valid time (min.) Note	t RD	0	0	0	0	0	ns
IORDY setup time (min.) Note	tA	35	35	35	35	35	ns
IORDY pulse width (max.) Note	tв	1250	1250	1250	1250	1250	ns
IORDY Inactive to Hi-Z time (max.) Note	tc	5	5	5	5	5	ns

Note IORDY is an option in mode 0 - 2. IORDY is essential in modes 3 and 4.

Multi Word DMA mode

Parameter	Symbol	Mode 0	Mode 1	Mode 2	Unit
Cycle time (min.)	to	480	150	120	ns
DIOR/DIOW pulse width (min.)	t⊳	215	80	70	ns
DIOR data access time (max.)	t⊨	150	60	50	ns
DIOR data hold time (min.)	t⊧	5	5	5	ns
DIOR data setup time (min.)	t _{Gr}	100	30	20	ns
DIOW data setup time (min.)	t _{Gw}	100	30	20	ns
DIOW data hold time (min.)	t⊦	20	15	10	ns
DMACK setup time (min.)	tı	0	0	0	ns
DMACK hold time (min.)	tu	20	5	5	ns
DIOR negate pulse width (min.)	t ĸr	50	50	25	ns
DIOW negate pulse width (min.)	tкw	215	50	25	ns
DIOR-DMARQ delay time (max.)	t∟r	120	40	35	ns
DIOW-DMARQ delay time (max.)	t∟w	40	40	35	ns
DMACK 3-state delay time (max.)	tz	20	25	25	ns
CS setup time (min.)	tм	50	30	25	ns
CS hold time (min.)	t⊳	15	10	10	ns

Ultra DMA mode

Parameter	Symbol Mo		ode 0 Mode 1		Mode 2		Mode 3		Mode 4		Unit	
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Average cycle time for 2 cycles	t2CYC	240	-	160	-	120	-	90	-	60	-	ns
Minimum cycle time for 2 cycles	t2CYC	235	-	156	-	117	-	86	-	57	-	ns
Cycle time for 1 cycle	tcyc	114	-	75	-	55	-	39	-	25	-	ns
Data setup time on receive side	tos	15	-	10	-	7	-	7	-	5	-	ns
Data hold time on receive side	tон	5	-	5	-	5	-	5	-	5	-	ns
Data setup time on transmit side	tovs	70	-	48	-	34	-	20	-	6	-	ns
Data hold time on transmit side	tovн	6	-	6	-	6	-	6	-	6	-	ns
First STROBE time	t⊧s	0	230	0	200	0	170	0	130	0	120	ns
Interlock time with limitation	t⊔	0	150	0	150	0	150	0	100	0	100	ns
Minimum interlock time	tmli	20	-	20	-	20	-	20	-	20	-	ns
Interlock time without limitation	tui	0	-	0	-	0	-	0	-	0	-	ns
Output release time	taz	-	10	-	10	-	10	-	10	-	10	ns
Output delay time	tzaн	20	-	20	-	20	-	20	-	20	-	ns
Output stabilization time (from release)	tzad	0	-	0	-	0	-	0	-	0	-	ns
Envelope time	t env	20	70	20	70	20	70	20	55	20	55	ns
STROBE DMARDY delay time	tsr	-	50	-	30	-	20	-	NA	-	NA	ns
Last STROBE time	trfs	-	75	-	60	-	50	-	60	-	60	ns
Pause time	trp	160	-	125	-	100	-	100	-	100	-	ns
IORDY pull-up time	tioryz	-	20	-	20	-	20	-	20	-	20	ns
IORDY wait time	tziory	0	-	0	-	0	-	0	-	0	-	ns
DMACK setup/hold time	tаск	20	-	20	-	20	-	20	-	20	-	ns
STROBE STOP time	tss	50	-	50	-	50	-	50	-	50	-	ns

Serial ROM interface Block

Parameter	Symbol	Conditions	Min.	Max.	Unit
Clock frequency	tsc∟			100	KHz
Clock pulse width low	t LOW		4.7		μs
Clock pulse width high	tніgн		4.0		μs
Clock Low to data valid	taa		100	4500	ns
Start hold time	thd.sta		4.0		μs
Start setup time	tsu.sta		4.7		μs
Data in hold time	thd.dat		0		ns
Data in setup time	tsu.dat		0.2		μs
Data out hold time	tон		50		ns
Stop setup time	tsu.sto		4.7		μs
Time the bus must be free before a new transmission can start	tbuf		10		μs
Write cycle time	twr		10		ms

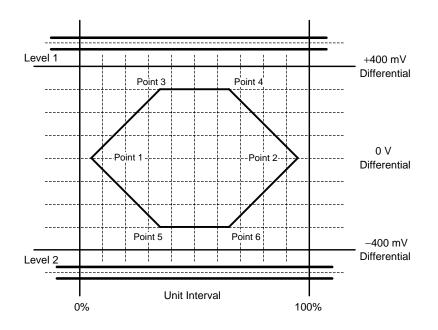
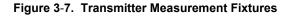
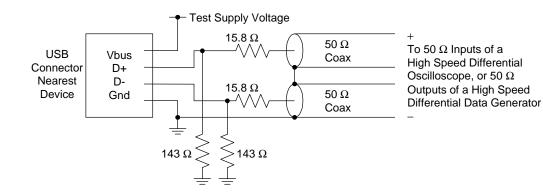


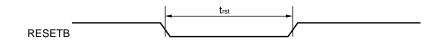
Figure 3-6. Transmit Waveform for Transceiver at DP/DM





Timing Diagram

System reset timing

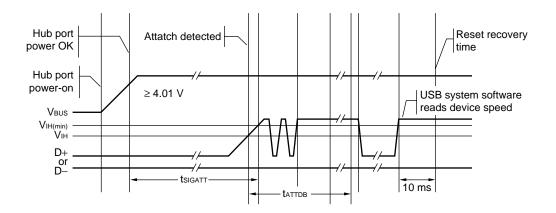


Remark After chip RESET, this chip reads the serial ROM first. Do not reset while the serial ROM is read. The read operation is completed in the period, which is calculated with the following expression.

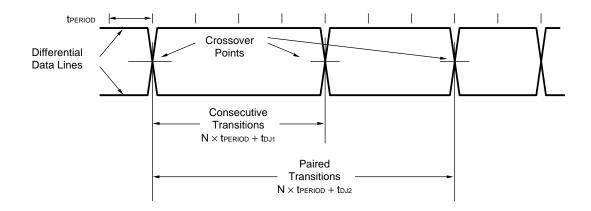
 $5 + 0.1197 \times \text{bytes} \text{ (serial ROM size)} + 0.5678 \text{ (ms)}$

Example In the case of 512 bytes: 66.855 ms, in the case of 8 Kbytes: 986.15 ms

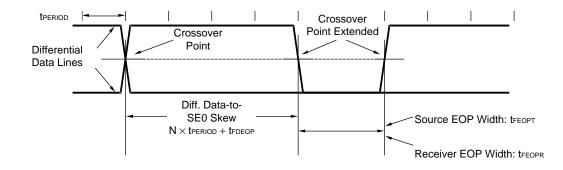
USB power-on and connection events



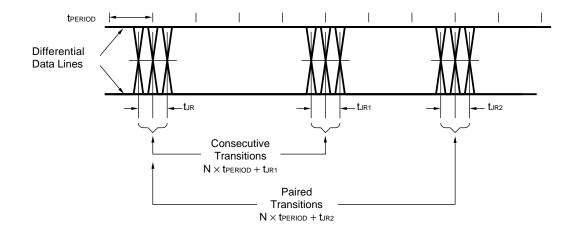
USB differential data jitter for full-speed



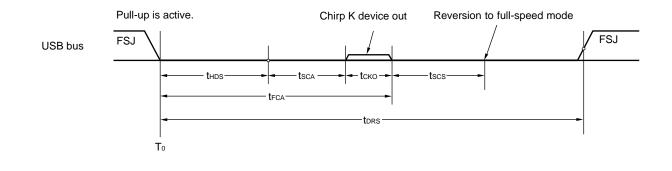
USB differential-to-EOP transition skew and EOP width for full-speed



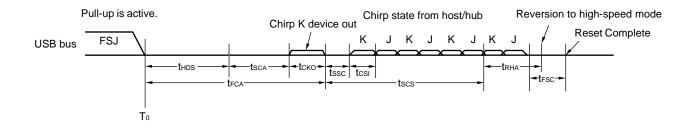
USB receiver jitter tolerance for full-speed



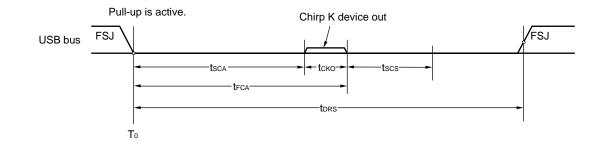
USB connection sequence on full-speed system bus



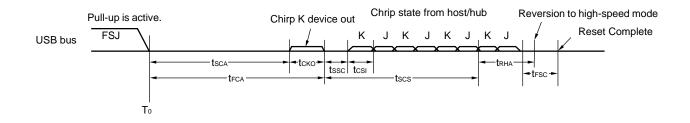
USB connection sequence on high-speed system bus



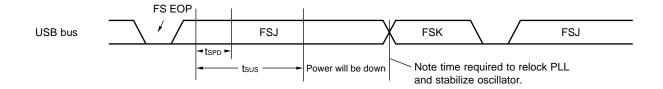
USB reset sequence from suspend state on full-speed system bus



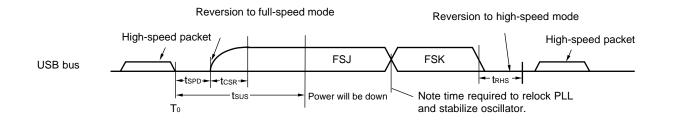
USB reset sequence from suspend state on high-speed system bus



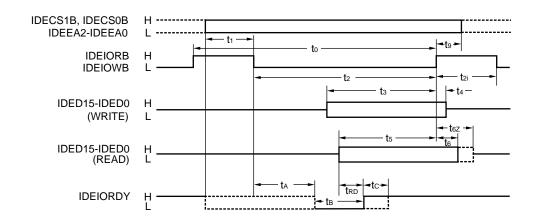
USB suspend and resume on full-speed system bus



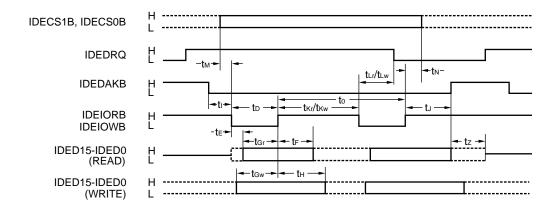
USB suspend and resume on high-speed system bus



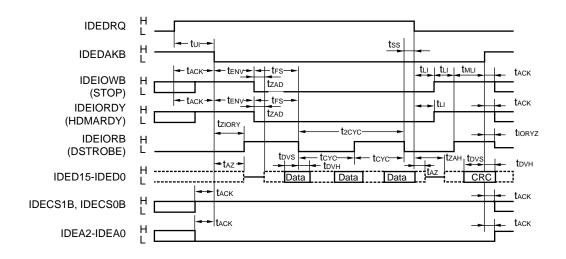
IDE PIO mode timing



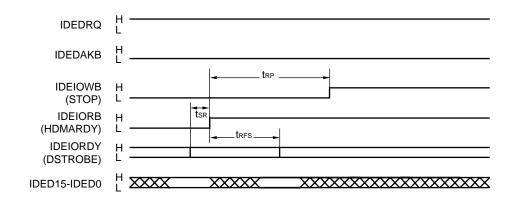
IDE multi word DMA mode timing



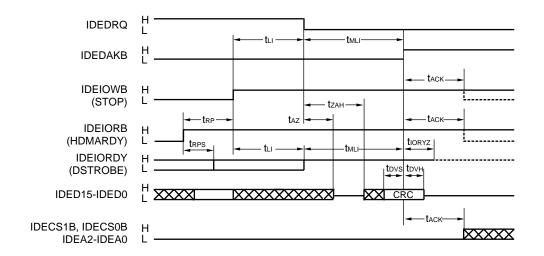
IDE ultra DMA mode data-in timing



IDE ultra DMA mode data-in stop timing

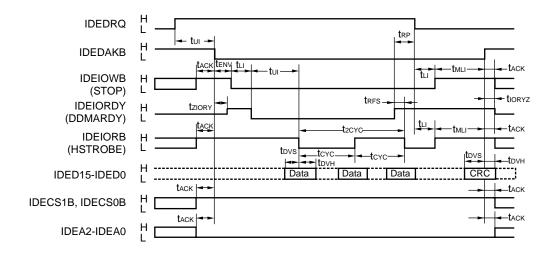


IDE ultra DMA mode data-in end timing

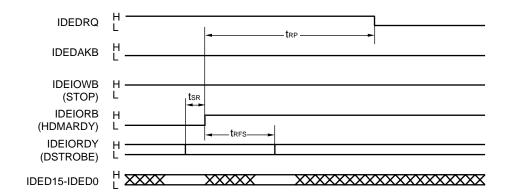


IDE ultra DMA mode data-out timing

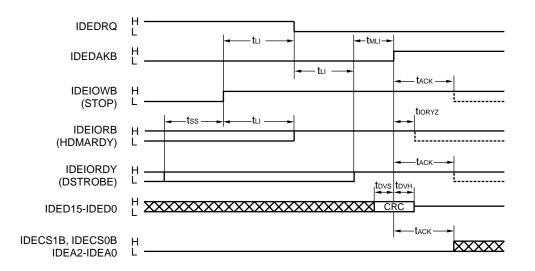
NEC



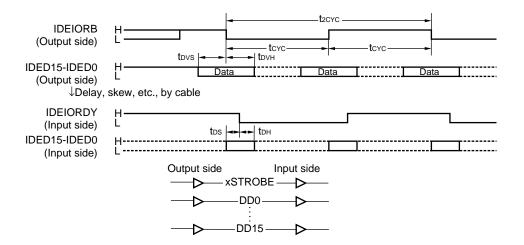
IDE ultra DMA mode data-out stop timing

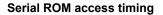


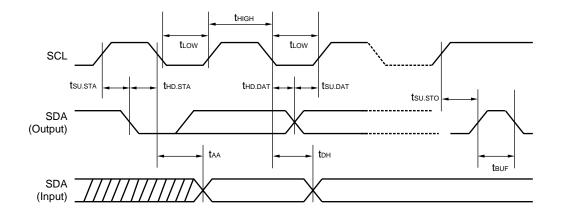
IDE ultra DMA mode data-out end timing



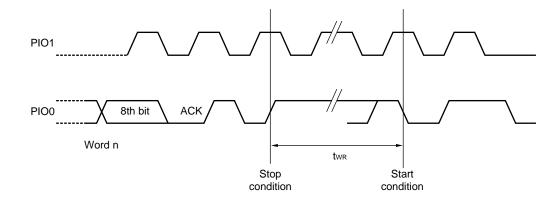
IDE ultra DMA mode data skew timing







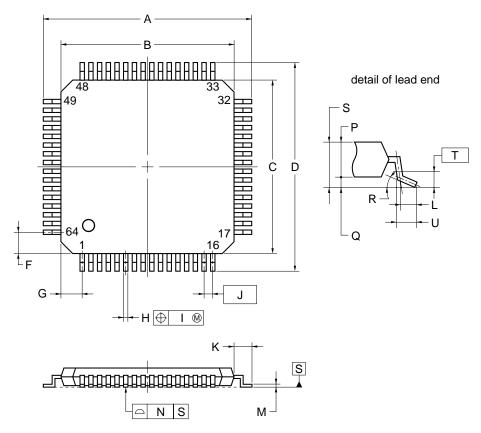
Serial ROM write cycle timing



4. PACKAGE DRAWING

- μPD720133GB-YEU-A
- µPD720133GB-YEU-Y

64-PIN PLASTIC TQFP (FINE PITCH) (10x10)



NOTE

Each lead centerline is located within 0.08 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
Α	12.0±0.2
В	10.0±0.2
С	10.0±0.2
D	12.0±0.2
F	1.25
G	1.25
Н	$0.22{\pm}0.05$
I	0.08
J	0.5 (T.P.)
К	1.0±0.2
L	0.5
М	$0.17\substack{+0.03 \\ -0.07}$
N	0.08
Р	1.0
Q	0.1±0.05
R	$3^{\circ + 4^{\circ}}_{-3^{\circ}}$
S	1.10±0.10
Т	0.25
U	0.6±0.15
	S64GB-50-YEU-1

5. RECOMMENDED SOLDERING CONDITIONS

The μ PD720133 should be soldered and mounted under the following recommended conditions.

For soldering methods and conditions other than those recommended below, please contact your NEC Electronics sales representative.

For technical information, please refer to the following website.

Semiconductor Device Mount Manual (http://www.necel.com/pkg/en/mount/index.html)

\muPD720133GB-YEU-A / μ PD720133GB-YEU-Y:64-pin plastic TQFP (Fine pitch) (10 × 10)

Soldering Method	Soldering Conditions					
Infrared reflow	Package peak temperature Time at peak temperature Time at 220°C or higher Preheat time (160 to 180°C) Maximum count Exposure limit	: 260°C : within 10 seconds : within 60 seconds : 60 to 120 seconds : 3 times or less : 3 days ^{Note} (after that, prebake at 125°C for 10 hours)	IR60-103-3			
Partial heating	g Pin temperature: 300°C max., Time: 3 seconds or less (per pin row)					

Note After opening the dry pack, store it at 25°C or less and 65% RH or less for the allowable storage period.

[MEMO]

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NOTES FOR CMOS DEVICES —

1 VOLTAGE APPLICATION WAVEFORM AT INPUT PIN

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (MAX) and V_{IH} (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (MAX) and V_{IH} (MIN).

(2) HANDLING OF UNUSED INPUT PINS

Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

③ PRECAUTION AGAINST ESD

A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

④ STATUS BEFORE INITIALIZATION

Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

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